5. (Amended) A light-emitting semiconductor device using a group III nitride group compound semiconductor according to claim 2, wherein a composition ratio y of gallium (Ga) in said quantum barrier layer is one of $y=1$, $y\approx1$, and $0.9<y\leq1$.

9. (Amended) A light-emitting semiconductor device using a group III nitride group compound semiconductor according to claim 2, wherein said composition ratio z of indium (In) in said quantum barrier layer is one of $z=0$, $z\approx0$, and $0\leq z<0.1$.

11. (Amended) A light-emitting semiconductor device using a group III nitride group compound semiconductor according to claim 5, wherein said composition ratio z of indium (In) in said quantum barrier layer is one of $z=0$, $z\approx0$, and $0\leq z<0.1$.

28. (Amended) A light-emitting semiconductor device using a group III nitride group compound semiconductor according to claim 1, wherein said composition ratio x of indium (In) in said quantum well layer is $0.15\leq x\leq0.6$.

29. (Amended) A light-emitting semiconductor device using a group III nitride group compound semiconductor according to claim 2, wherein said composition ratio x of indium (In) in said quantum well layer is $0.15\leq x\leq0.6$.

30. (Amended) A light-emitting semiconductor device using a group III nitride group compound semiconductor according to claim 5, wherein said composition ratio x of indium (In) in said quantum well layer is $0.15\leq x\leq0.6$.

32. (Amended) A light-emitting semiconductor device using a group III nitride group compound semiconductor according to claim 9, wherein said composition ratio x of indium (In) in said quantum well layer is $0.15\leq x\leq0.6$.

33. (Amended) A light-emitting semiconductor device using a group III nitride group compound semiconductor according to claim 11, wherein said composition ratio x of indium

(In) in said quantum well layer is $0.15 \leq x \leq 0.6$.

35. (Amended) A light-emitting semiconductor device using a group III nitride group compound semiconductor according to claim 1, wherein said composition ratio x of indium (In) in said quantum well layer is $0.15 \leq x \leq 0.5$.

36. (Amended) A light-emitting semiconductor device using a group III nitride group compound semiconductor according to claim 2, wherein said composition ratio x of indium (In) in said quantum well layer is $0.15 \leq x \leq 0.5$.

Please add the following new claims:

- - 39. A light-emitting semiconductor device comprising:

a substrate;

a plurality of semiconductor layers formed on said substrate, said layers comprising a group III nitride group compound semiconductor; and

an active layer comprising at least one quantum well layer comprising $Al_{1-x}In_xN$, where $0.1 \leq x \leq 1$.

40. A light-emitting semiconductor device according to claim 39, wherein said active layer further comprises at least one quantum barrier layer comprising $Al_{1-z-y}Ga_yIn_zN$ ($0 \leq y \leq 1$, $0 \leq z < 1$, $0 \leq z+y \leq 1$) which is adjacent to said at least one quantum well layer.

41. A light-emitting semiconductor device according to claim 40, wherein said at least one quantum well layer comprises a plurality of quantum well layers comprising $Al_{1-x}In_xN$, where $0.1 \leq x \leq 1$, and

wherein said at least one quantum barrier layer comprises a plurality of quantum barrier layers comprising $Al_{1-z-y}Ga_yIn_zN$ ($0 \leq y \leq 1$, $0 \leq z < 1$, $0 \leq z+y \leq 1$), and alternately formed with said plurality of quantum well layers.

42. A light-emitting semiconductor device according to claim 41, wherein said plurality

of quantum well layers comprises two quantum well layers having a thickness of about 4nm and comprising $Al_{0.80}In_{0.2}N$, and

wherein said plurality of quantum barrier layers comprises three quantum barrier layers having a thickness of about 6nm and comprising GaN.

Cancel.

43. A group III nitride group compound semiconductor device comprising:

a substrate; and

a light-emitting layer formed on said substrate, said light-emitting layer comprising:

a plurality of quantum well layers comprising $Al_{1-x}In_xN$, where $0.1 \leq x \leq 1$; and

a plurality of quantum barrier layers comprising $Al_{1-z-y}Ga_yIn_zN$ ($0 \leq y \leq 1$, $0 \leq z < 1$, $0 \leq z+y \leq 1$), which are alternately formed with said plurality of quantum well layers. - -